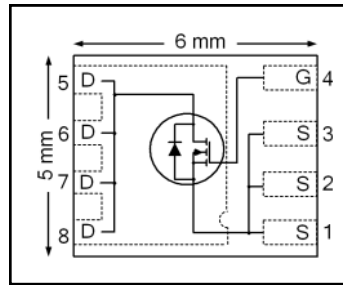


HEXFET® Power MOSFET

Application

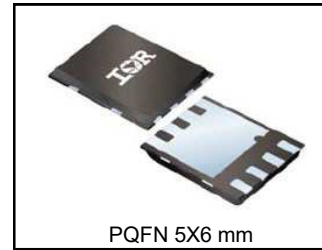
- Half-bridge and full-bridge topologies
- Synchronous rectifier applications
- Resonant mode power supplies
- DC/DC converters
- DC/AC Inverters



V_{DSS}	60V
R_{DS(on)} typ.	2.6mΩ
	max
I_D	147A

Benefits

- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and dI/dt Capability
- Lead-Free, RoHS Compliant



Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFH7085PbF	PQFN 5mm x 6mm	Tape and Reel	4000	IRFH7085TRPbF

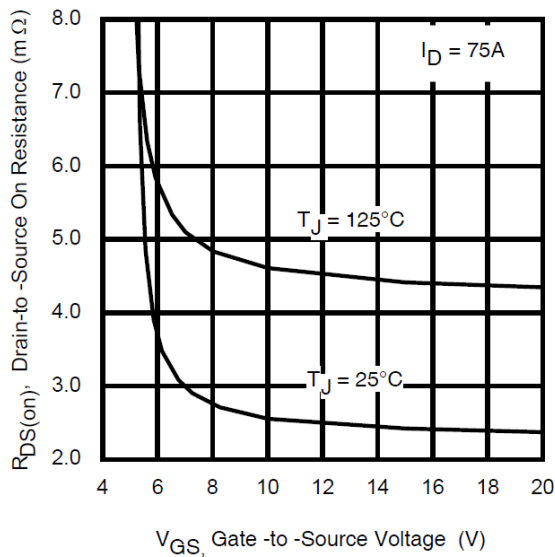


Fig 1. Typical On-Resistance vs. Gate Voltage

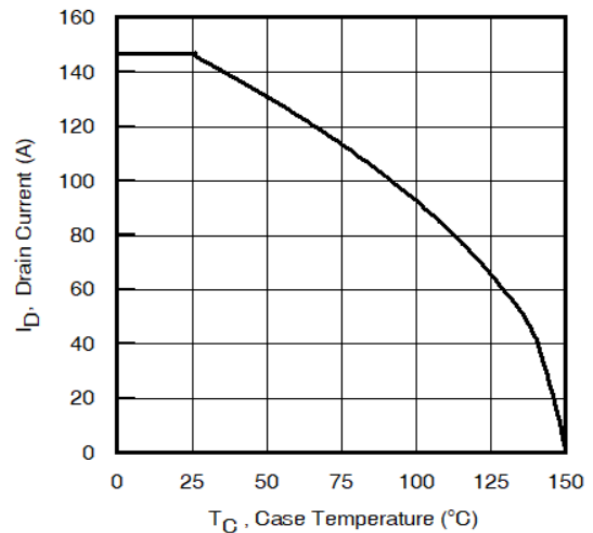


Fig 2. Maximum Drain Current vs. Case Temperature

Absolute Maximum Rating

Symbol	Parameter	Max.	Units
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	23	A
$I_D @ T_{C(\text{Bottom})} = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ ①	147	
$I_D @ T_{C(\text{Bottom})} = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ ①	93	
I_{DM}	Pulsed Drain Current ②	588	A
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	156	W
	Linear Derating Factor	1.25	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Avalanche Characteristics

Symbol	Parameter	Max.	Units
E_{AS} (Thermally limited)	Single Pulse Avalanche Energy ③	319	mJ
E_{AS} (Thermally limited)	Single Pulse Avalanche Energy ④	554	
I_{AR}	Avalanche Current ②	See Fig 15, 16, 23a, 23b	A
E_{AR}	Repetitive Avalanche Energy ②		mJ

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (Bottom)	Junction-to-Case ⑧	0.5	0.8	°C/W
$R_{\theta JC}$ (Top)	Junction-to-Case ⑧	—	20	
$R_{\theta JA}$	Junction-to-Ambient ⑩	—	34	
$R_{\theta JA} (<10\text{s})$	Junction-to-Ambient	—	22	

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	60	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	43	—	mV/°C	Reference to 25°C , $I_D = 1.0\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	2.6	3.2	mΩ	$V_{GS} = 10\text{V}, I_D = 75\text{A}$
		—	3.6	—		$V_{GS} = 6.0\text{V}, I_D = 38\text{A}$
$V_{GS(th)}$	Gate Threshold Voltage	2.1	—	3.7	V	$V_{DS} = V_{GS}, I_D = 150\mu\text{A}$
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$
		—	—	150		$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20\text{V}$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20\text{V}$
R_G	Gate Resistance	—	1.4	—	Ω	

Notes:

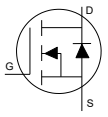
- ① Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature at 25°C . For higher case temperature please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 113\mu\text{H}$, $R_G = 50\Omega$, $I_{AS} = 75\text{A}$, $V_{GS} = 10\text{V}$.
- ④ $I_{SD} \leq 75\text{A}$, $di/dt \leq 1280\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$.
- ⑤ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ⑥ C_{oss} eff. (TR) is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑦ C_{oss} eff. (ER) is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑧ R_{θ} is measured at T_J approximately 90°C .
- ⑨ Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 1\text{mH}$, $R_G = 50\Omega$, $I_{AS} = 33\text{A}$, $V_{GS} = 10\text{V}$.
- ⑩ When mounted on 1 inch square PCB (FR-4). Please refer to AN-994 for more details:

<http://www.inf.com/technical-info/appnotes/an-994.pdf>

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g _{fs}	Forward Transconductance	140	—	—	S	V _{DS} = 10V, I _D = 75A
Q _g	Total Gate Charge	—	110	165	nC	I _D = 75A V _{DS} = 30V V _{GS} = 10V
Q _{gs}	Gate-to-Source Charge	—	30	—		
Q _{gd}	Gate-to-Drain Charge	—	36	—		
Q _{sync}	Total Gate Charge Sync. (Q _g - Q _{gd})	—	74	—		
t _{d(on)}	Turn-On Delay Time	—	13	—	ns	V _{DD} = 30V I _D = 30A R _G = 2.7Ω V _{GS} = 10V ^⑤
t _r	Rise Time	—	25	—		
t _{d(off)}	Turn-Off Delay Time	—	63	—		
t _f	Fall Time	—	23	—		
C _{iss}	Input Capacitance	—	6460	—	pF	V _{GS} = 0V V _{DS} = 25V f = 1.0MHz V _{GS} = 0V, V _{DS} = 0V to 48V ^⑦ V _{GS} = 0V, V _{DS} = 0V to 48V ^⑥
C _{oss}	Output Capacitance	—	560	—		
C _{rss}	Reverse Transfer Capacitance	—	380	—		
C _{oss eff.(ER)}	Effective Output Capacitance (Energy Related)	—	570	—		
C _{oss eff.(TR)}	Output Capacitance (Time Related)	—	715	—		

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	130	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ^②	—	—	588		
V _{SD}	Diode Forward Voltage	—	—	1.2	V	T _J = 25°C, I _S = 75A, V _{GS} = 0V ^⑤
dv/dt	Peak Diode Recovery dv/dt ^④	—	3.0	—	V/ns	T _J = 150°C, I _S = 75A, V _{DS} = 60V ^⑤
t _{rr}	Reverse Recovery Time	—	31	—	ns	T _J = 25°C V _{DD} = 51V T _J = 125°C I _F = 75A, di/dt = 100A/μs ^⑤
Q _{rr}	Reverse Recovery Charge	—	39	—		
I _{RRM}	Reverse Recovery Current	—	1.9	—	A	T _J = 25°C

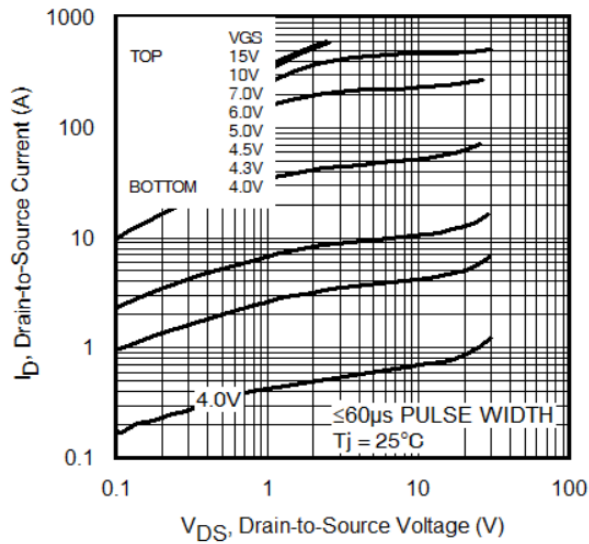


Fig 3. Typical Output Characteristics

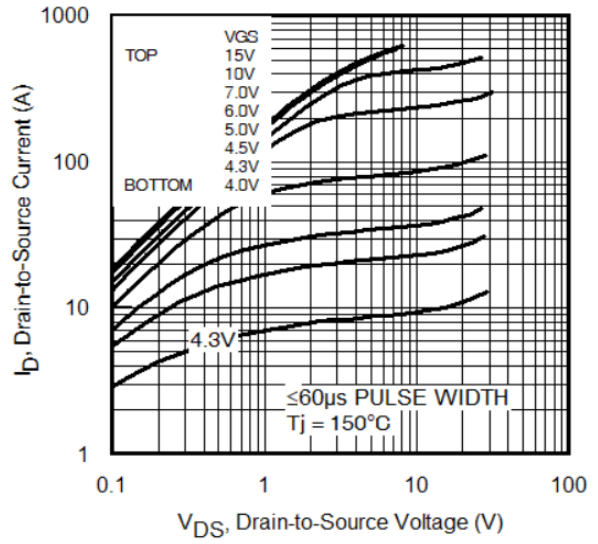


Fig 4. Typical Output Characteristics

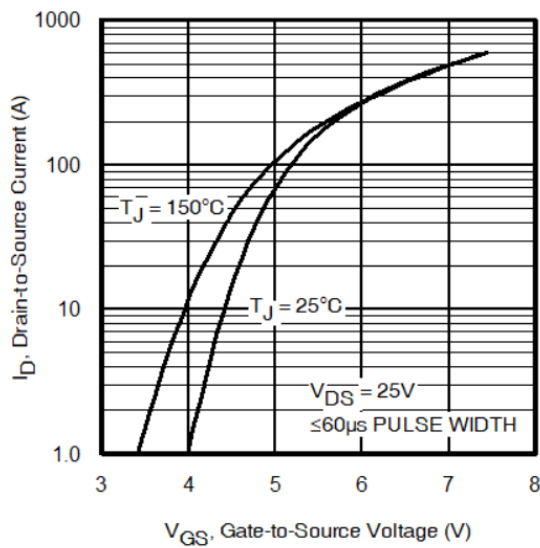


Fig 5. Typical Transfer Characteristics

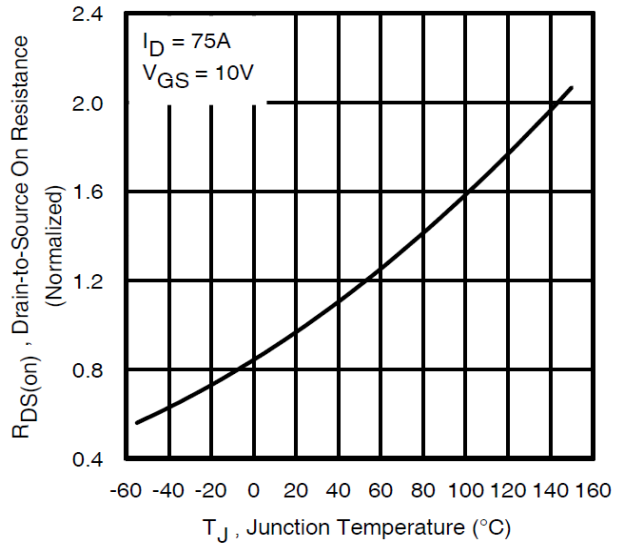


Fig 6. Normalized On-Resistance vs. Temperature

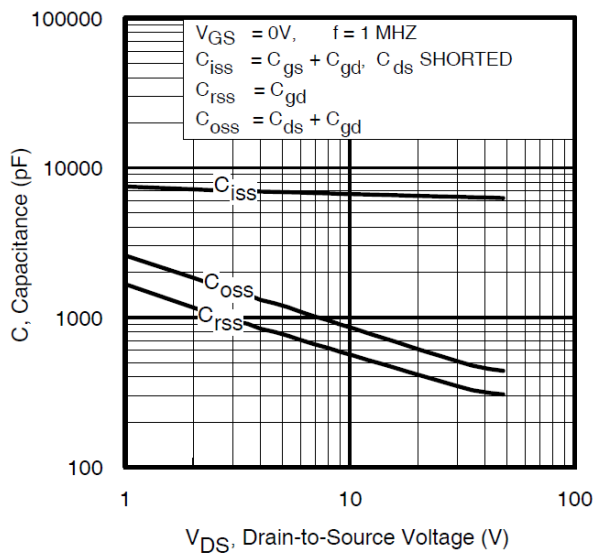


Fig 7. Typical Capacitance vs. Drain-to-Source Voltage

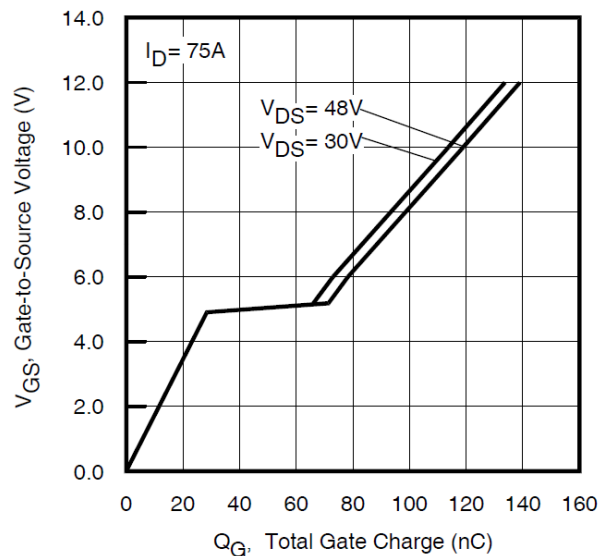


Fig 8. Typical Gate Charge vs. Gate-to-Source Voltage

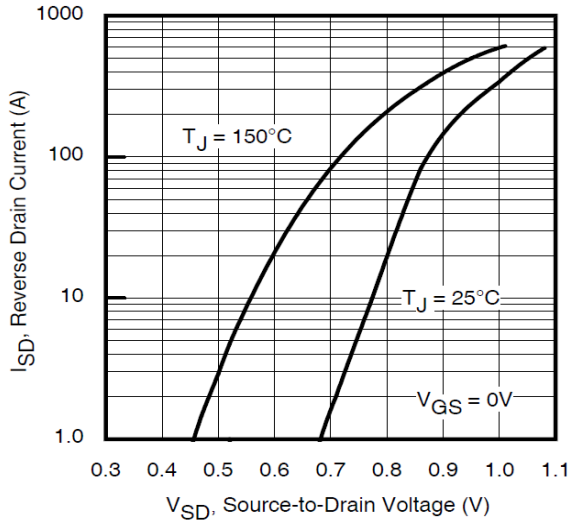


Fig 9. Typical Source-Drain Diode Forward Voltage

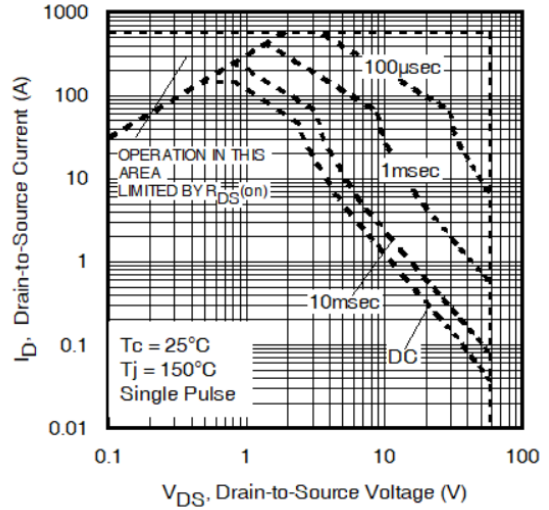


Fig 10. Maximum Safe Operating Area

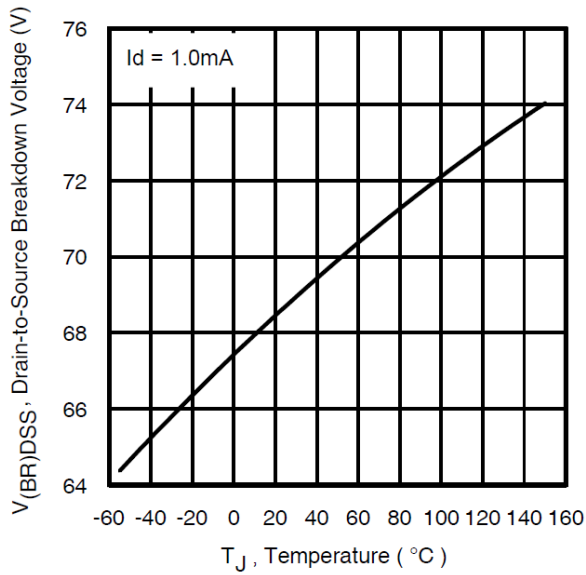


Fig 11. Drain-to-Source Breakdown Voltage

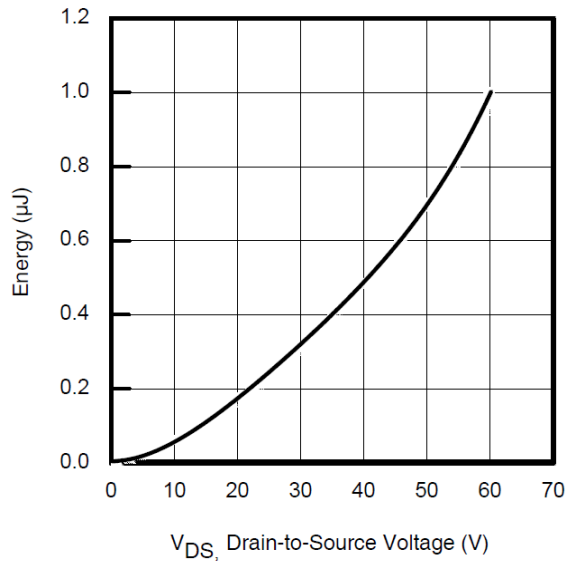


Fig 12. Typical C_{oss} Stored Energy

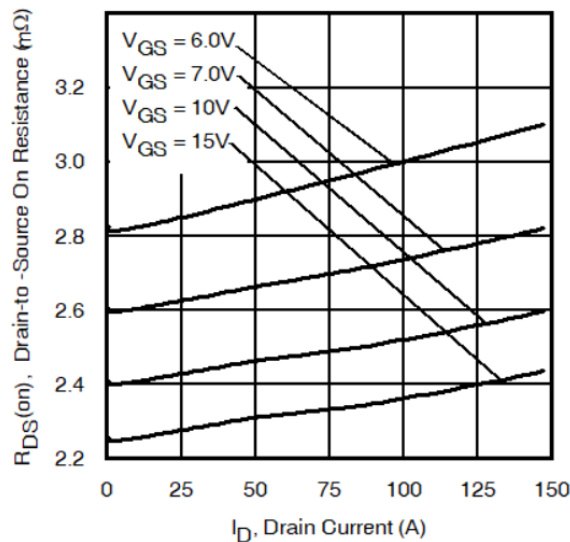


Fig 13. Typical On-Resistance vs. Drain Current

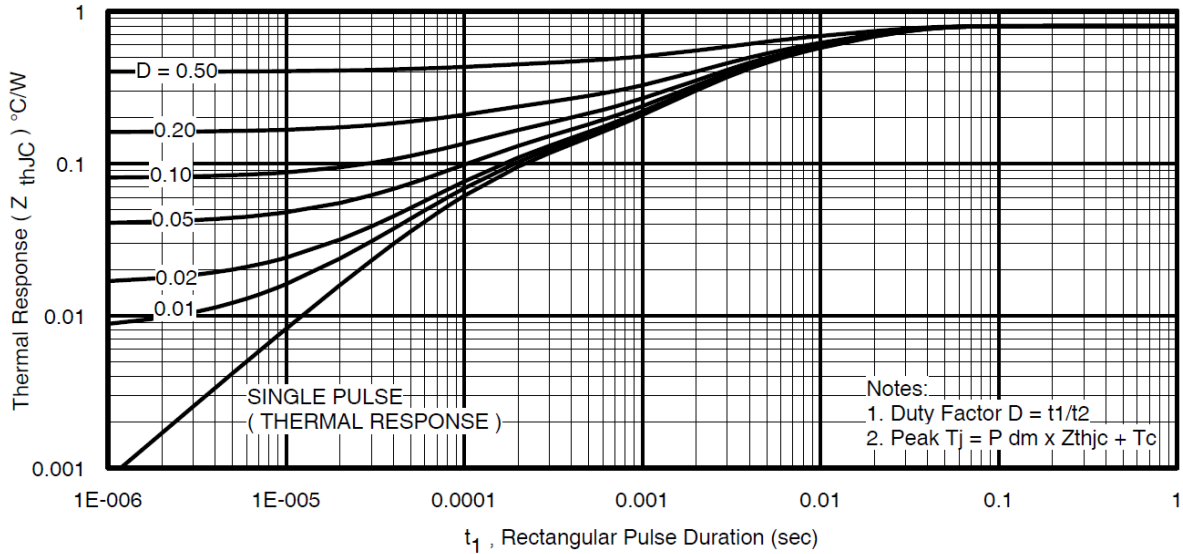


Fig 14. Maximum Effective Transient Thermal Impedance, Junction-to-Case

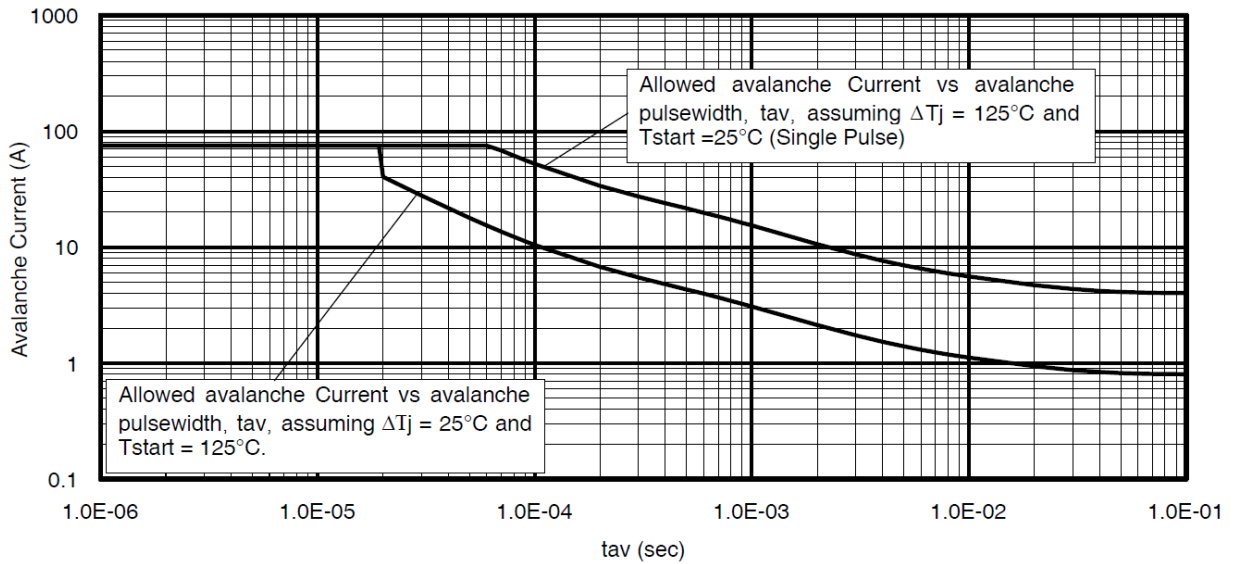
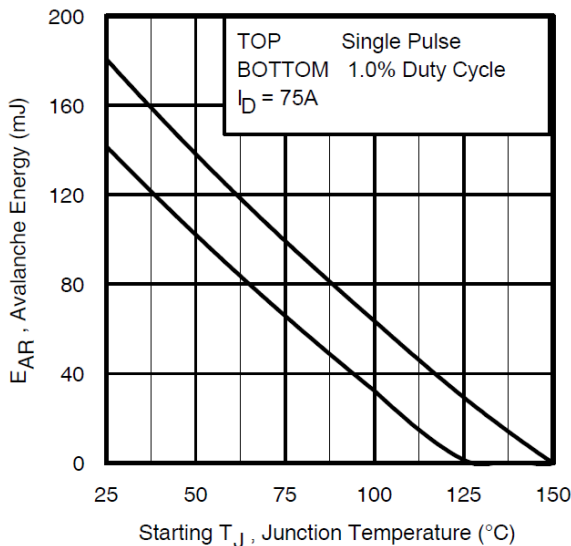


Fig 15. Typical Avalanche Current vs. Pulse Width



Notes on Repetitive Avalanche Curves, Figures 15, 16:
 (For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption: Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 22a, 22b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 16).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)
 $P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$
 $I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$
 $E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$

Fig 16. Maximum Avalanche Energy vs. Temperature

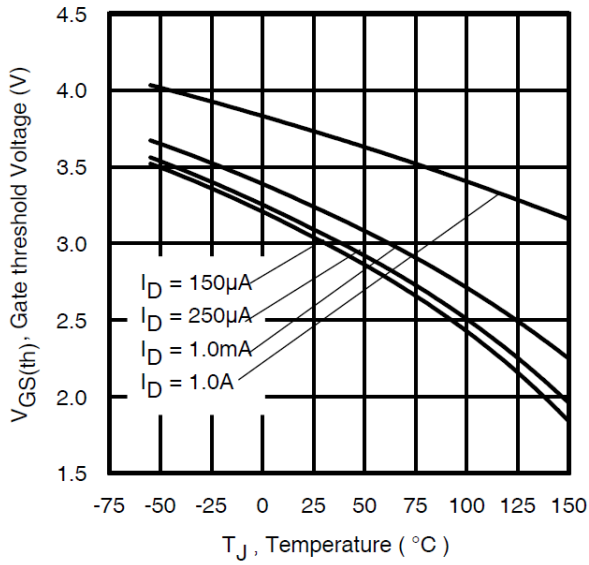


Fig 17. Threshold Voltage vs. Temperature

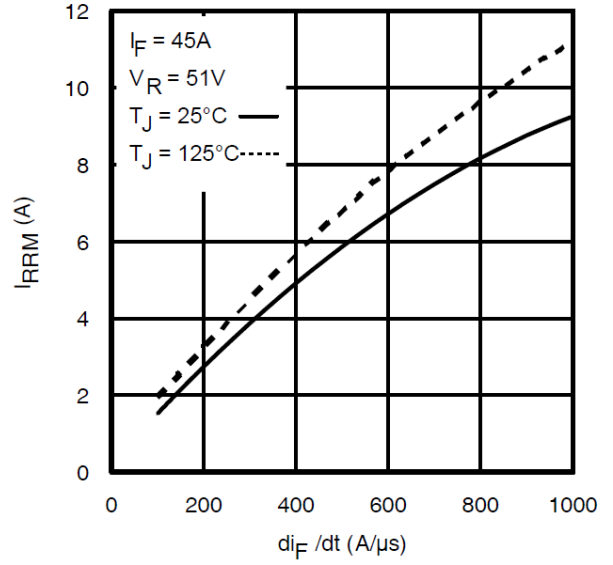


Fig 18. Typical Recovery Current vs. dif/dt

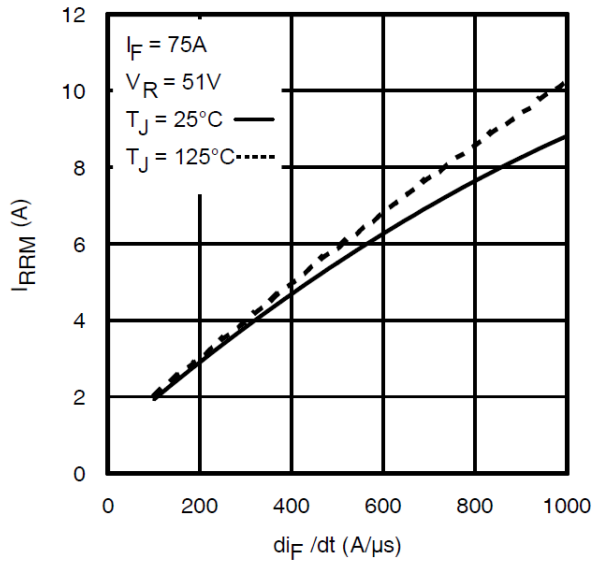


Fig 19. Typical Recovery Current vs. dif/dt

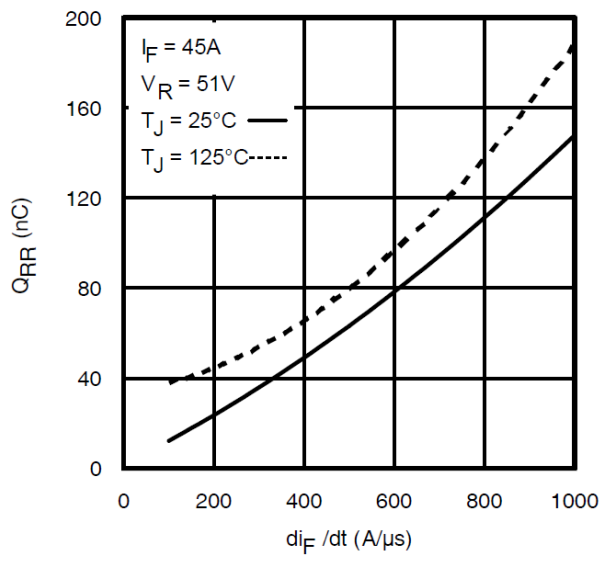


Fig 20. Typical Stored Charge vs. dif/dt

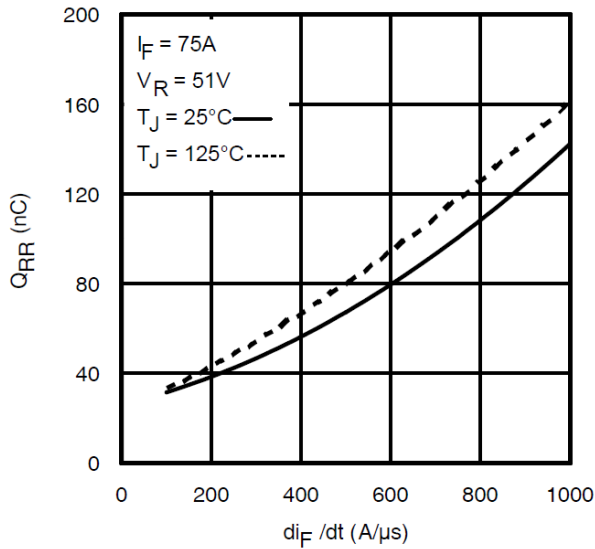


Fig 21. Typical Stored Charge vs. dif/dt

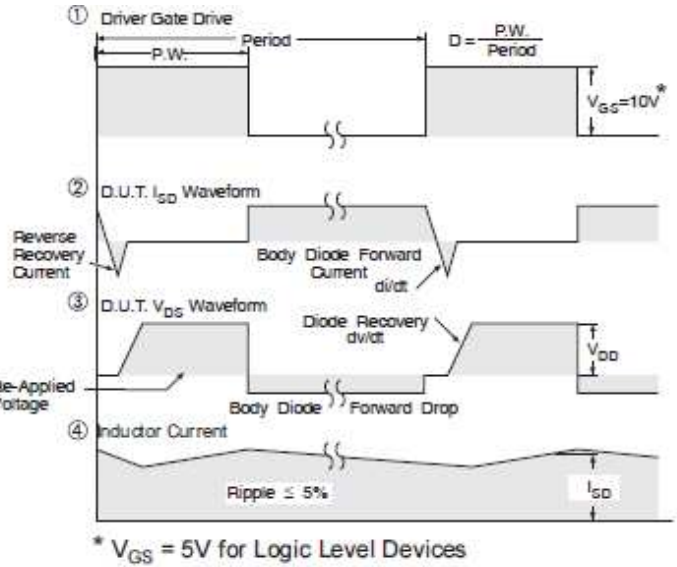
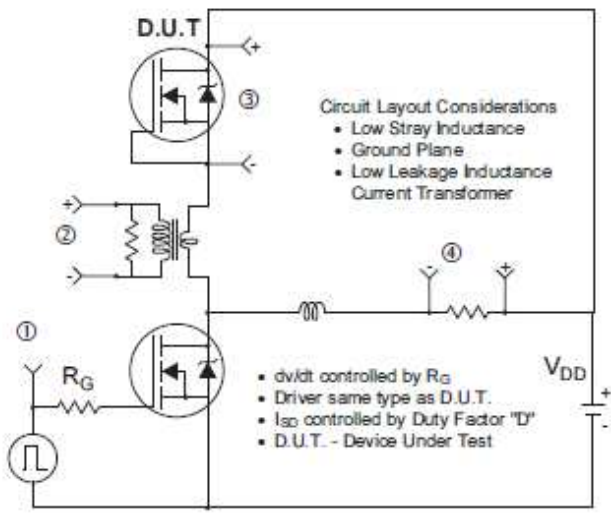


Fig 22. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

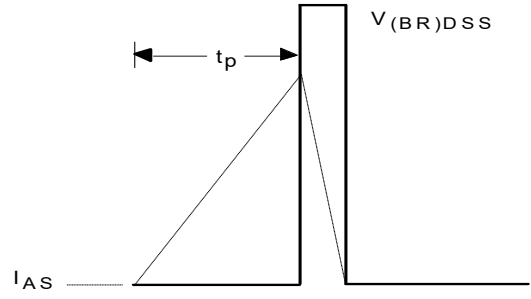
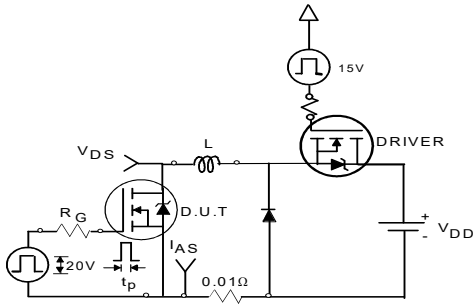


Fig 23a. Unclamped Inductive Test Circuit

Fig 23b. Unclamped Inductive Waveforms

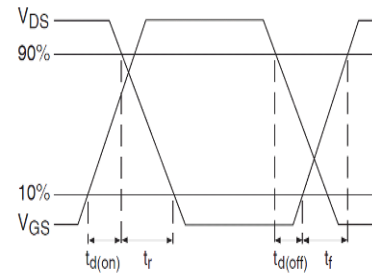
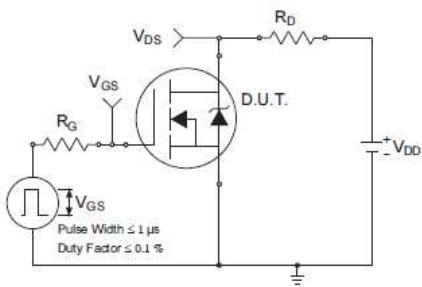


Fig 24a. Switching Time Test Circuit

Fig 24b. Switching Time Waveforms

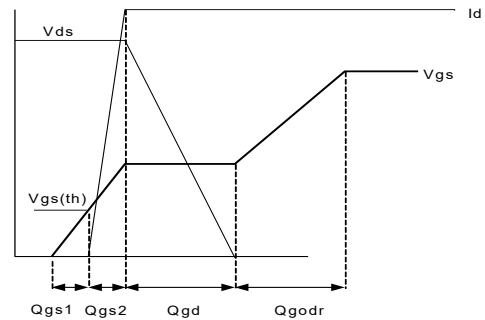
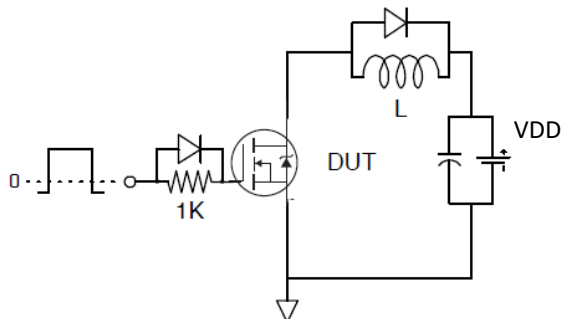
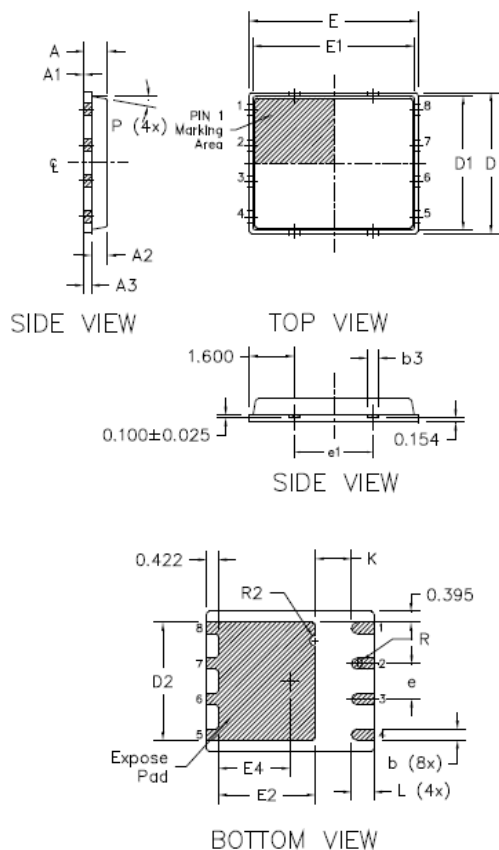


Fig 25a. Gate Charge Test Circuit

Fig 25b. Gate Charge Waveform

PQFN 5x6 Outline "B" Package Details



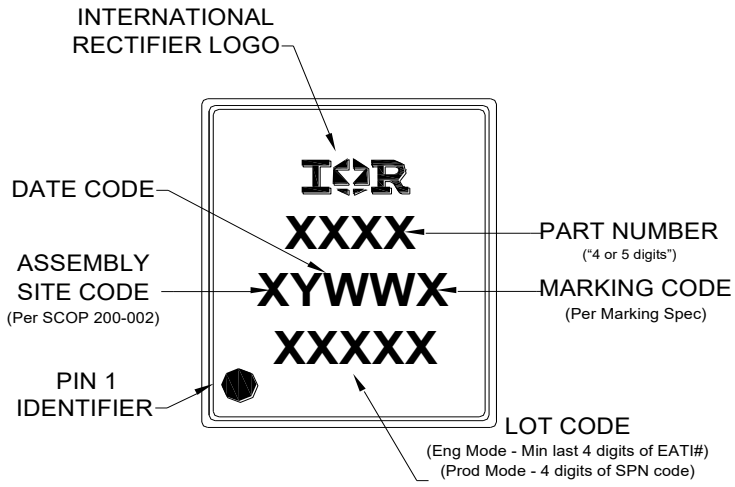
DIM SYMBOL	MILLIMETERS		INCH	
	MIN	MAX	MIN	MAX
A	0.800	0.900	0.0315	0.0543
A1	0.000	0.050	0.0000	0.0020
A3	0.200 REF		0.0079	REF
b	0.350	0.470	0.0138	0.0185
b1	0.025	0.125	0.0010	0.0049
b2	0.210	0.410	0.0083	0.0161
b3	0.150	0.450	0.0059	0.0177
D	5.000 BSC		0.1969 BSC	
D1	4.750 BSC		0.1870 BSC	
D2	4.100	4.300	0.1614	0.1693
E	6.000 BSC		0.2362 BSC	
E1	5.750 BSC		0.2264 BSC	
E2	3.380	3.780	0.1331	0.1488
e	1.270 REF		0.0500 REF	
e1	2.800 REF		0.1102 REF	
K	1.200	1.420	0.0472	0.0559
L	0.710	0.900	0.0280	0.0354
P	0°	12°	0°	12°
R	0.200 REF		0.0079 REF	
R2	0.150	0.200	0.0059	0.0079

- Note:
1. Dimensions and tolerancing confirm to ASME Y14.5M-1994
 2. Dimension L represents terminal full back from package edge up to 0.1mm is acceptable
 3. Coplanarity applies to the expose Heat Slug as well as the terminal
 4. Radius on terminal is Optional

For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136: <http://www.irf.com/technical-info/appnotes/an-1136.pdf>

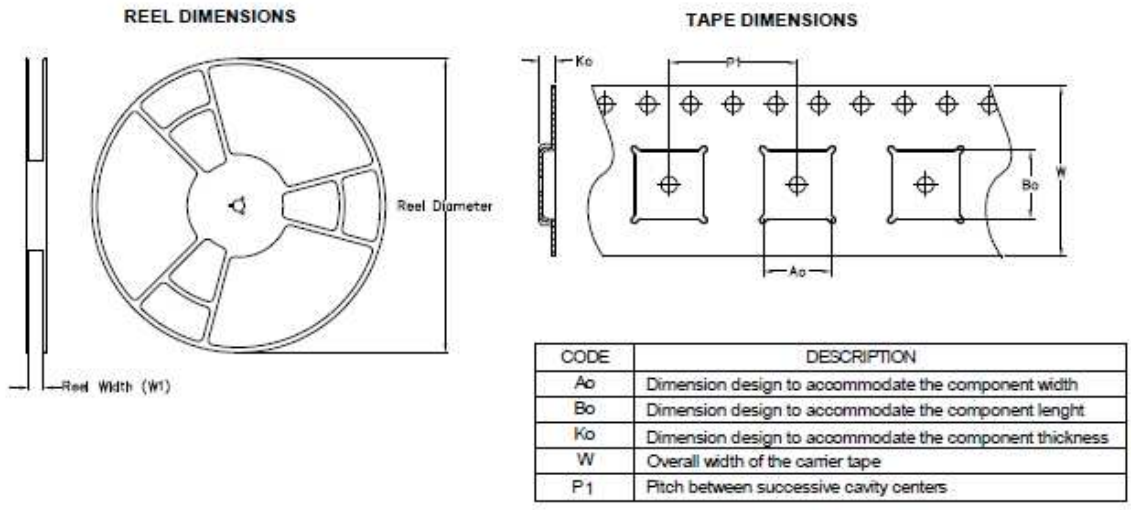
For more information on package inspection techniques, please refer to application note AN-1154: <http://www.irf.com/technical-info/appnotes/an-1154.pdf>

PQFN 5x6 Part Marking

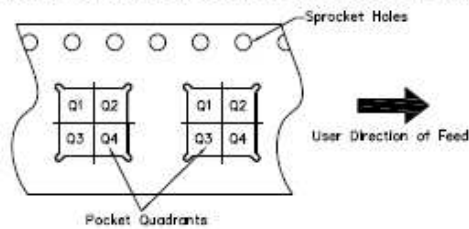


Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

PQFN 5x6 Tape and Reel



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Note: All dimension are nominal

Package Type	Reel Diameter (Inch)	QTY	Reel Width W1 (mm)	Ao (mm)	Bo (mm)	Ko (mm)	P1 (mm)	W (mm)	Pin 1 Quadrant
5 X 6 PQFN	13	4000	12.4	6.300	5.300	1.20	8.00	12	Q1

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information

Qualification level	Industrial (per JEDEC JESD47F † guidelines)	
Moisture Sensitivity Level	PQFN 5mm x 6mm	MSL1 (per JEDEC J-STD-020D†)
RoHS Compliant	Yes	

† Applicable version of JEDEC standard at the time of product release.

Revision History

Date	Rev.	Comments
11/7/2014	2.1	<ul style="list-style-type: none"> Added $E_{AS (L=1mH)} = 554mJ$ on page 2 Added note 9 "Limited by T_{Jmax}, starting $T_J = 25^{\circ}C$, $L = 1mH$, $R_G = 50\Omega$, $I_{AS} = 33A$, $V_{GS} = 10V$" on page 2 Added $P_d @ T_c = 25^{\circ}C$ on Absolute Max Rating table on page 2
3/17/2015	2.2	<ul style="list-style-type: none"> Updated package outline and tape and reel on pages 9 and 10.
4/16/2020	2.3	<ul style="list-style-type: none"> Updated datasheet based on IFX template. Updated Datasheet based on new current rating and application note :App-AN_1912_PL51_2001_180356

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